arc face, a radius of curvature thereof is determined to be equal to or larger

than 0.9 mm and an angle of an opening extended linearly from the bottom

portion and opened at the side face of the wafer is 90 degree. Further, also an

end edge of the opening is chamfered by [R] 0.9 mm and accordingly, a linear

portion except the circular arc face portion of the bottom portion of the notch 1

becomes 0.669 mm at maximum. --

IN THE CLAIMS:

Please replace Claims 1-5 with the following rewritten claims:

-- 1. A semiconductor wafer with a dot mark having a maximum length

of 1 to 13 µm on an inner wall face of a notch formed on an outer peripheral

face thereof. --

-- 2. The semiconductor wafer according to Claim 1, wherein upper and

lower edge line portions of the inner wall face of the notch are respectively

chamfered to thereby constitute upper and lower inclined faces and the dot

mark is formed on the inclined faces. --

-- 3. The semiconductor wafer according to Claim 2, wherein an angle of

an inclination of at least one inclined face relative to the surface of the

semiconductor wafer is equal to or smaller than 30 degrees. --

-- 4. The semiconductor wafer according to Claim 2, wherein a surface roughness of at least one inclined face is equal to or smaller than 1 µm. --

Cont.

-- 5. The semiconductor wafer according to Claim 2, wherein the dot mark is formed on either one of the upper and lower inclined faces. --

Please add the following new claims:

-- 6. The semiconductor wafer according to Claim 5, wherein an angle of an inclination of the inclined face relative to the surface of the semiconductor wafer is equal to or smaller than 30 degrees. --

-- 7. The semiconductor wafer according to Claim 5, wherein a surface roughness of the inclined face is equal to or smaller than 1 µm. --

-- 8. The semiconductor wafer according to Claim 1, wherein the dot mark is formed by irradiating a laser beam. --

-- 9. The semiconductor wafer according to Claim 1, wherein a dot mark has a height in the range of 0.005 to 5 µm. --

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